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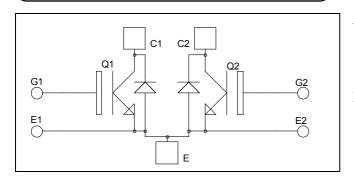








## Dual common source Trench + Field Stop IGBT3 Power Module



$$V_{CES} = 600V$$
  
 $I_{C} = 600A*$  @  $Tc = 80°C$ 

#### **Application**

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

#### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
$I_{\mathrm{C}}$	Continuous Collector Current	$T_C = 25^{\circ}C$	700 *	
	Continuous Conector Current	$T_C = 80$ °C	600 *	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	800	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25$ °C	2300	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	1200A @ 550V	

<sup>\*</sup> Specification of IGBT device but output current must be limited to 500A to not exceed a delta of temperature greater than 100°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				750	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.4	1.8	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_{\rm C} = 600 A$	$T_j = 150$ °C		1.5		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 2mA$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				800	nA

**Dynamic Characteristics** 

•	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			49		nF
$C_{oes}$	Output Capacitance				3.1		
$C_{res}$	Reverse Transfer Capacitance				1.5		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ning (25°C)		130		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			55		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_C = 600A$ $R_G = 2\Omega$			250		ns
$T_{\mathrm{f}}$	Fall Time				60		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_{C} = 600A$ $R_{G} = 2\Omega$			145		ns
$T_{r}$	Rise Time				60		
$T_{d(off)}$	Turn-off Delay Time				320		
$T_{\mathrm{f}}$	Fall Time				80		
Б	Turn on Energy	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		3		т
Eon		$V_{\text{Bus}} = 300\text{V}$	$T_{j} = 150^{\circ}C$		5.5		mJ
Б	Turn off Energy	$I_{\rm C} = 600 {\rm A}$	$T_j = 25^{\circ}C$		17		mJ
$E_{off}$		$R_G = 2\Omega$	$T_{j} = 150^{\circ}C$		21		1117

Reverse diode ratings and characteristics

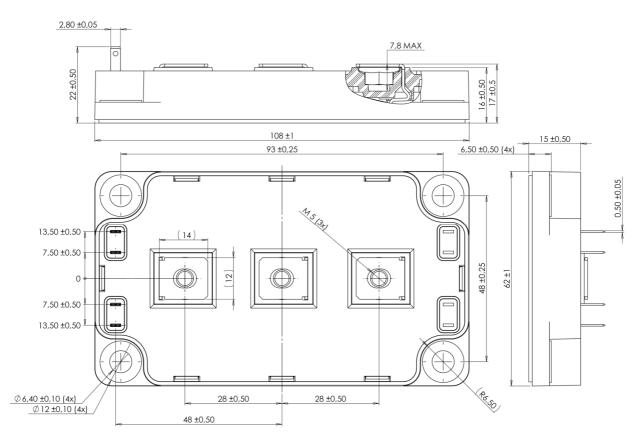
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_i = 25$ °C $T_i = 150$ °C			350 550	μΑ
$I_F$	DC Forward Current		$Tc = 80^{\circ}C$		600		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 600A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.5	1.9	V
<b>v</b> <sub>F</sub>			$T_{i} = 150^{\circ}C$		1.4		V
t <sub>rr</sub>	Reverse Recovery Time	$I_F = 600A$ $V_R = 300V$ $di/dt = 5000A/\mu s$	$T_j = 25$ °C		120		ne
ι <sub>rr</sub>			$T_j = 150$ °C		210		ns
0	Reverse Recovery Charge		$T_j = 25$ °C		27		иC
$Q_{rr}$			$T_{\rm j} = 150^{\circ}{\rm C}$		57		μС
Е	Payarsa Pagoyary Engray		$T_j = 25$ °C		6.9		mJ
$E_{r}$	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		14.1		1113



### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.065	°C/W
			Diode			0.11	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range Storage Temperature Range			-40		175	
$T_{STG}$				-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	11.111
Wt	Package Weight	·				300	g

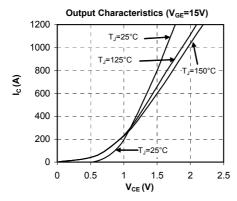
### SP6 Package outline (dimensions in mm)

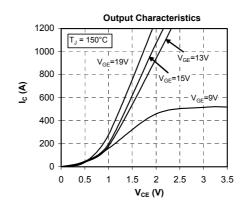


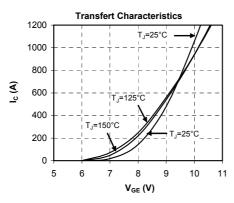
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

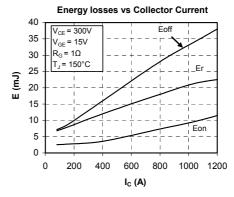


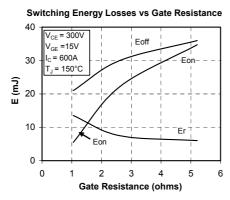
### **Typical Performance Curve**

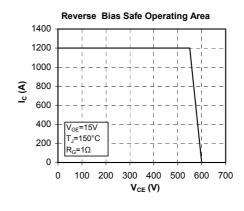


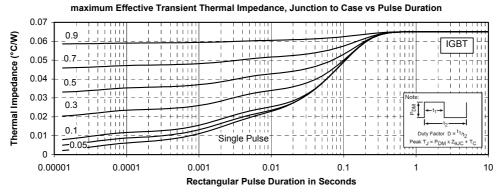




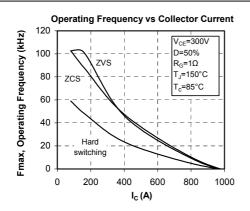


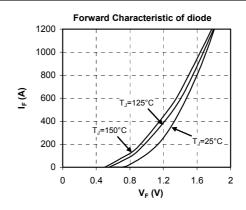


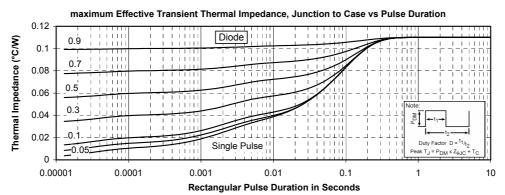














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